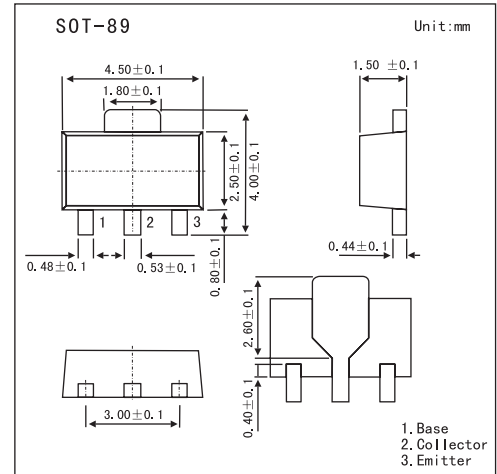


Silicon PNP Epitaxial Planar Type

2SB956

■ Features

- Large collector power dissipation P_C
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Peak collector current	I_{CP}	-2	A
Collector power dissipation	P_C	1	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	$I_C = -1 \text{ mA}, I_B = 0$	-20			V
Emitter-base voltage	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current	I_{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-1	nA
Forward current transfer ratio	h_{FE}	$V_{CE} = -2 \text{ V}, I_C = -500 \text{ mA}$	130		280	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			-1.2	V
Transition frequency	f_T	$V_{CB} = -6 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -6 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		40		pF

* Pulse measurement.

■ h_{FE} Classification

Marking	HR	HS
h_{FE}	130~210	180~280